Wideband, 43dB Isolation @ 1GHz, CMOS 1.65 V to 2.75V, 2:1 Mux/SPDT Switches

Preliminary Technical Data

FEATURES

ANALOG DEVICES

Wideband DC to 2GHz ADG918/ADG919 Absorptive/Reflective Switches High Off Isolation (43 dB @ 1 GHz) Low Insertion Loss (1 dB DC to 900 MHz) Single 1.65 to 2.75 V power supply CMOS/LVTTL Control Logic 8 Lead MSOP & Tiny 3 x 3mm CSP Packages Low Power Consumption (5µA)

APPLICATIONS

Wireless Communications General Purpose RF switching Dual Band Applications Filter Selection Antenna Switch Digital Transceiver Front-End Switch IF Switching

GENERAL DESCRIPTION

The ADG918/ADG919 are wideband switches using a CMOS process to provide high isolation and low insertion loss to 1GHz. The ADG918 is an absorptive switch having 50 ohm terminated shunt legs, while the ADG919 is a reflective switch. These devices are designed such that the isolation is high over the DC to 1GHz frequency range. They have on board CMOS control logic, thus eliminating the need for external controlling circuitry. The control inputs are both CMOS and LVTTL compatible. The low power consumption of these CMOS devices makes them ideally suited to wireless applications and general purpose high frequency switching.

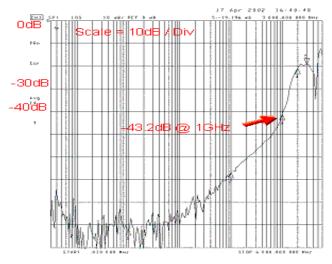


Figure 1. Isolation vs Frequency

REV. PrC Sept 2002

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices.

ADG918/ADG919

FUNCTIONAL BLOCK DIAGRAM

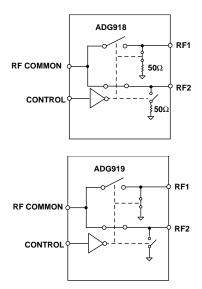


Table 1. Truth Table

Control	Signal Path				
0	RF2 to RF Common				
1	RF1 to RF Common				

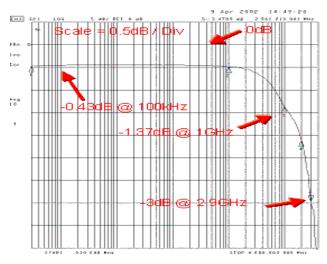


Figure 2. Loss vs Frequency

 One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.

 Tel: 781/329-4700
 www.analog.com

 Fax: 781/326-8703
 Analog Devices, Inc., 2002

PRELIMINARY TECHNICAL DATA

$\label{eq:spectral_add} \begin{array}{l} \textbf{ADG918/ADG919} \\ \textbf{-SPECIFICATIONS}^1 \\ (v_{\text{DD}} = +1.65 \text{ V to } +2.75 \text{ V}, \text{ GND} = 0 \text{ V}, \text{ All specifications } T_{\text{MIN}} \text{ to } T_{\text{MAX}} \text{ unless otherwise noted}) \end{array}$

			B Version			
Parameter	Symbol	Conditions	Min	Typ ²	Max	Units
AC ELECTRICAL CHARACTERISTICS						
Operating Frequency			DC		2	GHz
Insertion Loss	S_{21}, S_{12}	DC - 100 MHz		0.4		dB
	-	500 MHz		0.65		dB
		900 MHz		1.0		dB
Isolation- RF to RF1/RF2	S ₂₁ , S ₁₂	1 MHz		100		dB
		100 MHz		55		dB
		500 MHz				dB
		1000 MHz		43		dB
Isolation - RF1 to RF2	S ₂₁ , S ₁₂	1 MHz		100		dB
		100 MHz		55		dB
		500 MHz				dB
		1000 MHz		30		dB
Return Loss (On Channel)	S ₁₁ , S ₂₂	DC - 100 MHz		26		dB
		500 MHz				dB
		1000 MHz		23		dB
On switching Time	t _{ON}	50% Control to 90% RF		5		ns
Off Switching Time	t _{OFF}	50% Control to 10% RF		4		ns
1 dB Compression	P _{-1dB}	DC to 1000 MHz		20		dBm
Third Order Intermodulation intercept	IP ₃	900MHz, 5dBm		35		dBm
DC ELECTRICAL CHARACTERISTICS						
Input High Voltage	V _{INH}	$V_{DD} = 2.3 \text{ V}$ to 2.75 V	1.7			V
	V _{INH}	$V_{DD} = 1.65$ V to 1.95 V	0.65V _{CC}			V
Input Low Voltage	V _{INL}	$V_{DD} = 2.3 \text{ V}$ to 2.75 V			0.7	V
	V _{INL}	$V_{DD} = 1.65 \text{ V}$ to 1.95 V			$0.35V_{CC}$	V
Input Leakage Current	II	$0 \leq V_{IN} \leq 2.75 \ V$			±1	μA
CAPACITANCE ³						
RF1/RF2, RF Port On Capacitance	C _{RF} ON	f = 1 MHz		2		pF
Control Input Capacitance	C _{IN}	f = 1 MHz		2		pF
POWER REQUIREMENTS						
V _{DD}			1.65		2.75	V
Quiescent Power Supply Current	IDD	Digital Inputs = 0 V or V_{DD}		1	5	μA

NOTES

¹Temperature range is as follows: B Version: -40°C to +85°C.

² Typical values are at $+25^{\circ}$ C unless otherwise stated.

³ Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

ADG918/ADG919

ABSOLUTE MAXIMUM RATINGS¹

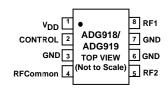
$(T_A = +25^{\circ}C \text{ unless otherwise noted})$)			
V _{DD} to GND	-0.5 V to +4 V			
Inputs to GND	-0.5 V to V _{DD} + 0.3V			
Input Power	TBD dBm			
Operating Temperature Range	:			
Industrial (B Version)	-40°C to +85°C			
Storage Temperature Range	-65°C to +150°C			
Junction Temperature	+150°C			
MSOP Package				
θ_{JA} Thermal Impedance	206°C/W			
CSP Package				
θ_{JA} Thermal Impedance	TBD°C/W			
Lead Temperature, Soldering	(10seconds) 300°C			
IR Reflow, Peak Temperature	(<20 seconds) +235°C			
NAMERO				

NOTES

¹Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

PIN CONFIGURATION

8-Lead MSOP (RM-8) 3x3mm CSP (CP-8)



ORDERING GUIDE

Model	Temperature Range	Package Descriptions	Branding	Package Options
ADG918BRM	-40°C to +85°C	MSOP (Micro Small Outline Package)		RM-8
ADG918BCP	-40°C to +85°C	Chip Scale Package		CP-8
ADG919BRM	-40°C to +85°C	MSOP (Micro Small Outline Package)		RM-8
ADG919BCP	-40°C to +85°C	Chip Scale Package		CP-8

CAUTION -

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG919 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



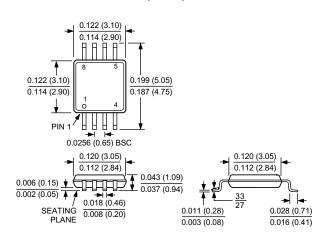
PRELIMINARY TECHNICAL DATA

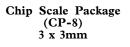
ADG918/ADG919

OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

MSOP (RM-8)





TBD